

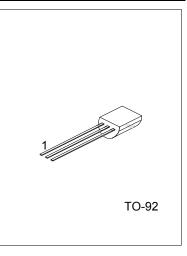
MPSA92M

PNP EPITAXIAL SILICON TRANSISTOR

HIGH VOLTAGE TRANSISTOR

FEATURES

- * Collector-Emitter voltage: V_{CEO}=-300V
- * Collector Dissipation: $P_{C(MAX)}$ =625mW
- * Low collector-Emitter saturation voltage



ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing		
Lead Free	Halogen Free		Fackage	1	2	3	Packing	
MPSA92ML-T92-B	MPSA92MG-T92-B		TO-92	Е	В	С	Tape Box	
MPSA92ML-T92-K	MPSA92MG-T92-K		TO-92	Е	В	С	Bulk	
MPSA92ML-T92-R	MPSA92MG-T92-R		TO-92	Е	В	С	Tape Reel	
Note: Pin Assignment: E:EMITTER B:BASE C:COLLECTOR								
MPSA92ML- <u>T92-B</u> (1)Packing Type (2)Package Type (3)Lead Free			 (1) B: Tape Box, K: Bulk, R: Tape Reel (2) T92: TO-92 (3) Halogen Free, L: Lead Free 					

■ ABSOLUTE MAXIMUM RATINGS (T_J=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V _{CBO}	-300	V
Collector-Emitter Voltage	V _{CEO}	-300	V
Emitter-Base Voltage	V _{EBO}	-6	V
Collector Dissipation (T _A =25°C)	Pc	625	mW
Collector Current	lc	-800	mA
Junction Temperature	TJ	150	°C
Storage Temperature	T _{STG}	-55~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =-100μΑ, I _E =0	-300			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =-1mA, I _B =0	-300			V
Collector-Emitter Breakdown Voltage	BV _{CES}	I _C =-100μA, V _{BE} =0	-300			V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E =-100μA, I _C =0	-5			V
Collector Cut-Off Current	I _{CBO}	V _{CB} =-300V, I _E =0			-100	nA
Collector Cut-Off Current	ICES	V _{CB} =-300V, V _{BE} =0			-1	μA
Emitter Cut-Off Current	I _{EBO}	V _{EB} =-4V, I _C =0			100	nA
DC Current Gain (Note 1)	h _{FE}	V _{CE} =-10V, I _C =-1mA	60			
		V _{CE} =-10V, I _C =-10mA	80		300	
		V _{CE} =-10V, I _C =-100mA	80			
		V _{CE} =-10V, I _C =-200mA	40			
	V _{CE(SAT)}	I _C =-30mA, I _B =-1mA			-0.20	V
Collector-Emitter Saturation Voltage		I _C =-100mA, I _B =-10mA		-0.7		
Base-Emitter Saturation Voltage	V _{BE(SAT)}	I _C =-10mA, I _B =-1mA			-0.75	V
Output Capacitance	Сов	V _{CB} =-20V, I _E =0, f=1MHz			8	pF

Note: 1. Pulse test: PW<300µs, Duty Cycle<2%

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